

### MSD23N58 N-Channel 60V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low RDS (on) and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

# G S



- Low rDS(on) provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe
- SOT-23 saves board space
- · Fast switching speed
- · High performance trench technology



Absolute Maximum Ratings (Tc=25°C unless otherwise noted)					
Parameter	Symbol	Value	Unit		
Drain-Source Voltage	VDS	60	V		
Gate-Source Voltage	VGS	±20	V		
Continuous Drain Current @ TC=25°C	ID	2.8	A		
Continuous Drain Current @ TC=70°C	ID	1.8	A		
Pulsed Drain Current	IDM	±15	A		
Continuous Source Current (Diode Conduction)	IS	1.7	A		
Power Dissipation (TC=25°C)	DD	1.3	W		
Power Dissipation (TC=100°C)	PD	0.8	W		
Operating Junction and Storage Temperature	Tj, Tstg	-55~+150	°C		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Thermal characteristics (Tc=25°C unless otherwise noted)				
Parameter	Symbol	Value	Unit	
Maximum Junatian to Ambient(DthIA)	t <= 5 sec	100	°C/W	
Maximum Junction-to-Ambient(RthJA)	Steady State	106		



Characteristics (Tc=25°C, unless otherwise specified)						
Symbol	<b>Test Conditions</b>	Min.	Тур.	Max.	Unit	
Static Characteristics						
VGS	VGS = VDS, $ID = 250  uA$	1.0	-	1	V	
IGSS	$VDS = 0 V$ , $VGS = \pm 20 V$	-	-	±100	nA	
IDSS	VDS = 48  V, VGS = 0  V	-	-	1.0	uA	
	VDS = 48 V, VGS = 0 V, T J = 55oC	-	-	50.0	uA	
ID(on)	VDS = 5 V, VGS = 10 V	10	-	-	A	
RDS(on)	VGS = 10 V, ID = 3.1 A	-	-	92	mΩ	
	VGS = 4.5 V, ID = 2.9 A	-	-	107	mΩ	
gfs	VDS = 4.5V, ID = 3.1 A	-	8	-	S	
VSD	IS = 1.7  A, VGS = 0  V	-	1.1	-	V	
Dynamic	Characteristics					
Qg		-	3.6	-	nC	
Qgs	VDS = 30  V, VGS = 5  V, ID = 3.1  A	-	1.8	-	nC	
Qgd		-	1.3	-	nC	
td(on)		-	10	-	nS	
tr	$VDD = 30 \text{ V}, RL = 30 \Omega, ID = 1 \text{ A},$	-	10	-	nS	
td(off)	VGEN = 10 V	-	20	-	nS	
tf		-	10	-	nS	

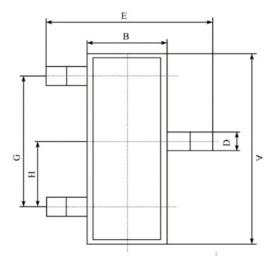
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

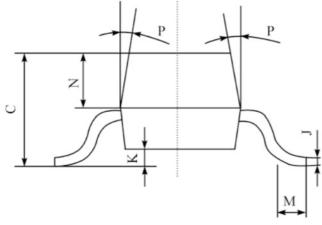


## Package Dimensions

#### SOT-23



Α	$2.90 \pm 0.10$
В	$1.30 \pm 0.10$
C	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
E	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
Н	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	0.00-0.10
M	≥0.2
N	$0.60 \pm 0.10$
P	7 ± 2°



Dimensions in millimeter